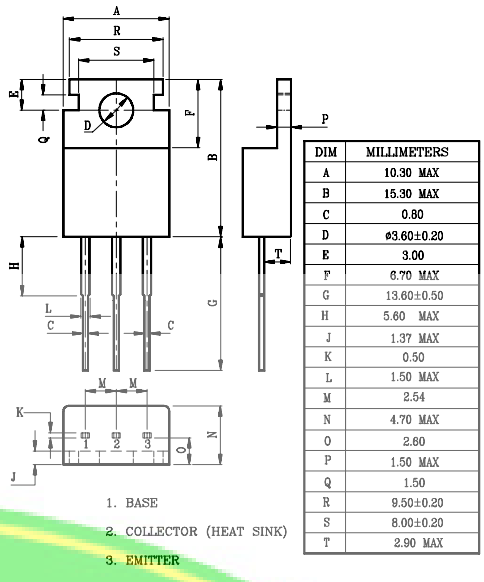
KTD1351

TRIPLE DIFFUSED NPN TRANSISTOR

GENERAL PURPOSE APPLICATION.

FEATURES

- Low Saturation Voltage
  : $V_{CE(sat)}$=1.0V(Max.) (I_C=2A, I_B=0.2A).
- Complementary to KTB988.



DIM	MILLIMETERS
A	10.30 MAX
B	15.30 MAX
C	0.80
D	ø3.60±0.20
E	3.00
F	6.70 MAX
G	13.60±0.50
H	5.60 MAX
J	1.37 MAX
K	0.50
L	1.50 MAX
M	2.54
N	4.70 MAX
O	2.60
P	1.50 MAX
Q	1.50
R	9.50±0.20
S	8.00±0.20
T	2.90 MAX

TO-220AB

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	60	V
Collector-Emitter Voltage		V_{CEO}	60	V
Emitter-Base Voltage		V_{EBO}	7	V
Collector Current		I_C	3	A
Base Current		I_B	0.5	A
Collector Power Dissipation	Ta=25℃	P_C	2	W
	Tc=25℃		30	
Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55~150	℃

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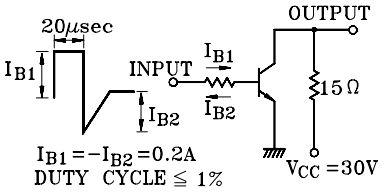
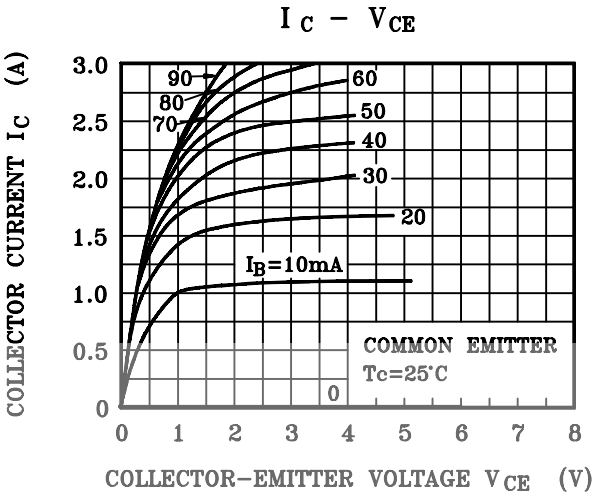
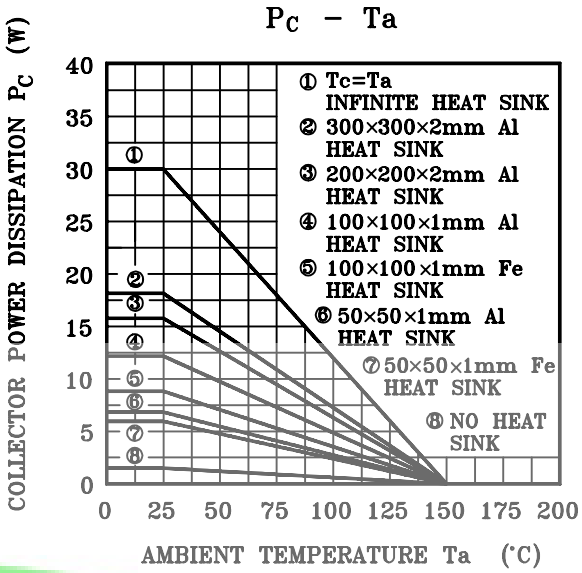
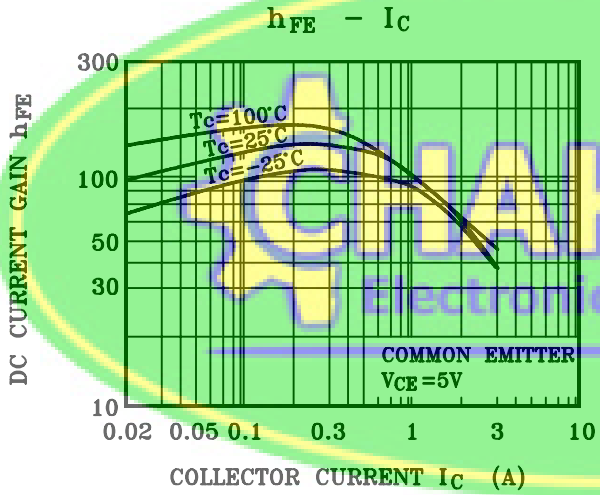
ELECTRICAL CHARACTERISTICS (Ta=25℃)

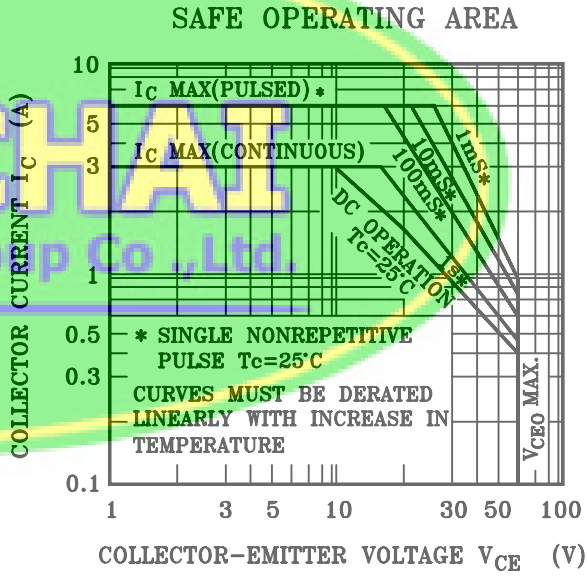
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	V_{CB}=60V, I_E=0	-	-	100	μA
Emitter Cut-off Current		I_{EBO}	V_{EB}=7V, I_C=0	-	-	100	μA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	I_C=50mA, I_B=0	60	-	-	V
DC current Gain		h_{FE}	V_{CE}=5V, I_C=0.5A (Note)	60	-	300	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	I_C=2A, I_B=0.2A	-	0.25	1.0	V
Base-Emitter Voltage		V_{BE}	V_{CE}=5V, I_C=0.5A	-	0.7	1.0	V
Transition Frequency		f_T	V_{CE}=5V, I_C=0.5A	-	3.0	-	MHz
Collector Output Capacitance		C_{ob}	V_{CB}=10V, I_E=0, f=1MHz	-	35	-	pF
Switching Time	Turn-on Time	t_{on}		-	0.65	-	μS
	Storage Time	t_{stg}		-	1.3	-	
	Fall Time	t_f		-	0.65	-	

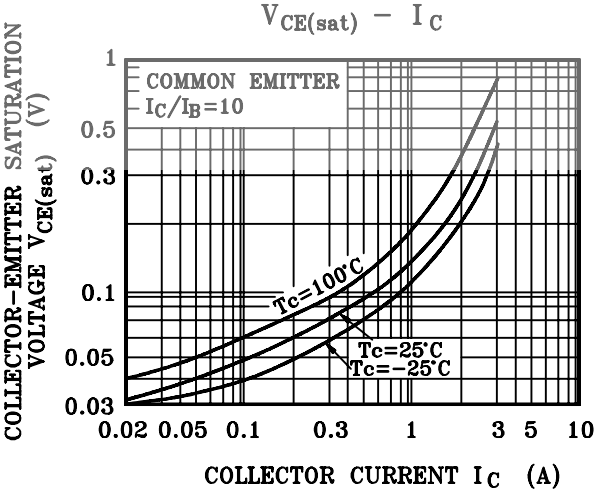
Note : h_{FE} Classification O:60~120, Y:100~200, GR:150~300











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